**DOCKET NO.:** 23085-08273 **PATENT** 

**Client Ref.:** H1023023US02

**USSN:** 10/658,711

## LISTING OF CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (Currently amended) A method for synthesizing <u>single wall carbon nanotubes</u>, the <u>method carbon nanostructures</u> comprising <u>the steps of</u>:

providing a substrate having a deposition mask;

depositing a bimetallic or trimetallic metalorganic layer on the substrate, wherein at least a portion of the bimetallic or trimetallic metalorganic layer is deposited on an unmasked portion of the substrate, and wherein the bimetallic or trimetallic metalorganic layer comprises an organic portion and an inorganic portion, and wherein the bimetallic or trimetallic metalorganic layer has a thickness between about 1 micron and about 30 microns;

removing the deposition mask from the substrate;

exposing said portion of the bimetallic or trimetallic metalorganic layer to air;

pyrolyzing the organic portion of said portion of the bimetallic or trimetallic metalorganic layer to form a growth catalyst on the substrate; and

exposing the substrate to a carbon precursor gas at a deposition temperature to form single wall carbon nanotubes carbon nanostructures.

- 2. (Currently amended) The method of claim 1, wherein the bimetallic or trimetallic metalorganic layer <u>comprises a metalorganic</u> [[is]] selected from the group consisting of: iron phthalocyanine, molybdenum phthalocyanine, nickel phthalocyanine, copper phthalocyanine, <u>or a combination and combinations</u> thereof.
- 3. (Previously Presented) The method of claim 1, wherein the bimetallic or trimetallic metalorganic layer is deposited by a physical vapor deposition process.
- 4. (Canceled)

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5. (Currently amended) The method of claim 1, wherein the deposition mask <u>comprises</u> is

composed of a metal oxide.

6. (Currently amended) The method of claim 1, wherein the deposition mask <u>comprises</u> is

composed of a substance selected from the group consisting of silicon oxide [[and]] or aluminum

oxide.

7. (Currently amended) The method of claim 1, wherein the unmasked portion of the

substrate has a top surface comprising composed of a metal oxide.

8. (Original) The method of claim 7, wherein the metal oxide is selected from the group

consisting of silicon oxide, aluminum oxide, and magnesium oxide.

9. (Currently amended) The method of claim 1, wherein the organic portion of said

portion of the bimetallic or trimetallic metalorganic layer is pyrolyzed by heating said portion of

the bimetallic or trimetallic metalorganic layer to a temperature of between about 450°C and

about 500°C.

10. (Currently amended) The method of claim 1, wherein said portion of the

bimetallic or trimetallic metalorganic layer is exposed to air for between about 2 hours to about 4

hours.

11. (Original) The method of claim 1, wherein the growth catalyst comprises metal

growth catalyst particles.

12. (Currently amended) The method of claim 1, wherein the carbon precursor gas

comprises [[is]] methane.

13. (Currently amended) The method of claim 1, wherein exposing the substrate to a carbon

precursor gas comprises exposing the substrate to an atmosphere comprising containing

methane, argon, and hydrogen.

14. (Currently amended) The method of claim 13, wherein the substrate is exposed to the

carbon precursor gas for between about 15 minutes and about 60 minutes.

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15. (Currently amended) The method of claim 1, wherein the deposition temperature is

about 700°C.

16. (Previously presented) The method of claim 1, wherein the bimetallic or

trimetallic metalorganic layer is produced by deposition of a metalorganic substance and the

metalorganic substance is purified prior to deposition of the bimetallic or trimetallic

metalorganic layer.

17. (Previously presented) The method of claim 1, wherein the exposing said

portion of the bimetallic or trimetallic metalorganic layer to air is performed prior to removing

the deposition mask from the substrate.

18. (Canceled)

19. (Currently amended) The method of claim 1, wherein said carbon nanostructures are

one-dimensional one dimensional carbon nanostructures.

20-42. (Canceled).

43. (New) The method of claim 1, wherein the bimetallic or trimetallic metalorganic layer

has a thickness of less than 5 microns.

44. (New) The method of claim 43, wherein the bimetallic or trimetallic metalorganic layer

has a thickness of 1 micron.

45. (New) The method of claim 43, wherein the bimetallic or trimetallic metalorganic layer

has a thickness of 2 microns.